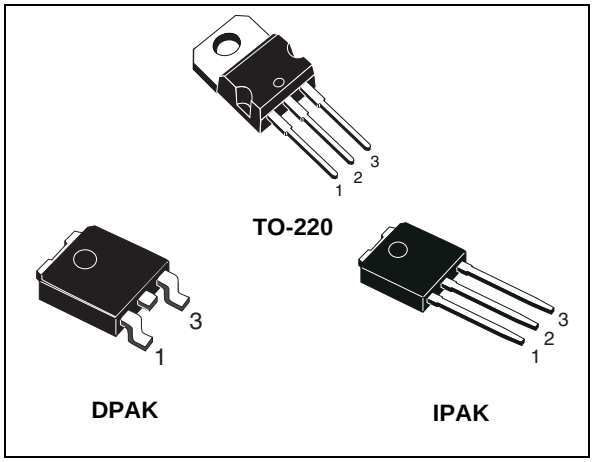
STD60N3LH5
STP60N3LH5, STU60N3LH5

N-channel 30 V, 0.0072 Ω, 48 A DPAK, IPAK, TO-220
STripFET™ V Power MOSFET

Features

Type	V_{DSS}	$R_{DS(on)}$ max	I_D
STD60N3LH5	30 V	0.008 Ω	48 A
STP60N3LH5	30 V	0.0084 Ω	48 A
STU60N3LH5	30 V	0.0084 Ω	48 A

- $R_{DS(on)}$ * Q_g industry benchmark
- Extremely low on-resistance $R_{DS(on)}$
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses



Application

- Switching applications

Description

This STripFET™V Power MOSFET technology is among the latest improvements, which have been especially tailored to achieve very low on-state resistance providing also one of the best-in-class FOM.

Figure 1. Internal schematic diagram

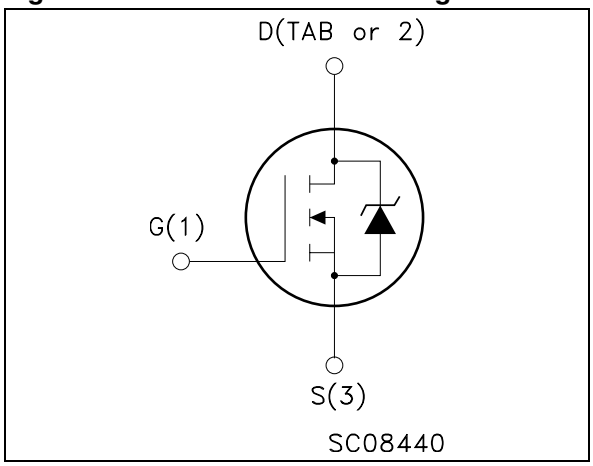


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD60N3LH5	60N3LH5	DPAK	Tape and reel
STP60N3LH5	60N3LH5	TO-220	Tube
STU60N3LH5	60N3LH5	IPAK	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS}=0)	30	V
V_{DS}	Drain-source voltage (V_{GS} = 0) @ T_{JMAX}	35	V
V_{GS}	Gate-Source voltage	± 22	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	48	A
I_D	Drain current (continuous) at T_C = 100 °C	42.8	A
I_{DM} (2)	Drain current (pulsed)	192	A
P_{TOT}	Total dissipation at T_C = 25 °C	60	W
	Derating factor	0.4	W/°C
E_{AS} (3)	Single pulse avalanche energy	160	mJ
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 175	°C

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting Tj = 25 °C, Id = 24 A, Vdd = 12 V

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case max	2.5	°C/W
Rthj-amb	Thermal resistance junction-case max	100	°C/W
T_j	Maximum lead temperature for soldering purpose	275	°C

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	I_D = 250 µA, V_{GS}= 0	30			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 30 V V_{DS} = 30 V,Tc = 125 °C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ± 22 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250 µA	1	1.8	3	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10 V, I_D= 24 A SMD version		0.0072	0.008	Ω
		V_{GS}= 10 V, I_D= 24 A		0.0076	0.0084	Ω
		V_{GS}= 5 V, I_D= 24 A SMD version		0.0088	0.011	Ω
		V_{GS}= 5 V, I_D= 24 A		0.0092	0.0114	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25 V, f=1 MHz, V_{GS}=0	-	1350 265 32	-	pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}=15 V, I_D = 48 A V_{GS} =5 V	-	8.8 4.7 2.2	-	nC nC nC
Q_{gs1} Q_{gs2}	Pre V_{th} gate-to-source charge Post V_{th} gate-to-source charge	V_{DD}=15 V, I_D = 48 A V_{GS} =5 V	-	2.2 2.5	-	nC nC
R_G	Gate input resistance	f=1 MHz gate bias Bias= 0 test signal level=20 mV open drain	-	1.1	-	Ω

Table 6. Switching on/off (resistive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD}=10 V, I_D= 24 A, R_G=4.7 Ω, V_{GS}= 10 V	-	6 33	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	V_{DD}=10 V, I_D= 24 A, R_G=4.7 Ω, V_{GS}= 10 V	-	19 4.2	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}	Source-drain current Source-drain current (pulsed)(1)		-		48 192	A A
V_{SD}	Forward on voltage	I_{SD}=24 A, V_{GS}=0	-		1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=48 A, di/dt =100 A/µs, V_{DD}=20 V,	-	25 18.5 1.5		ns nC A

1. Pulsed: pulse duration = 300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

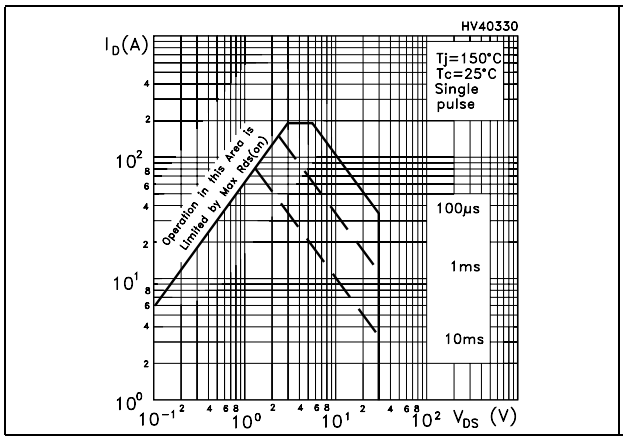


Figure 3. Thermal impedance

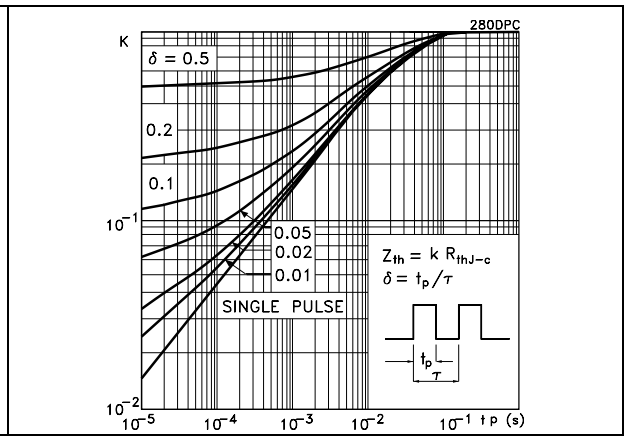


Figure 4. Output characteristics

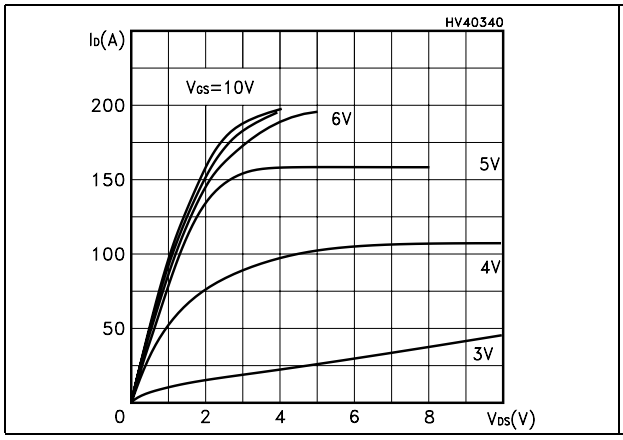


Figure 5. Transfer characteristics

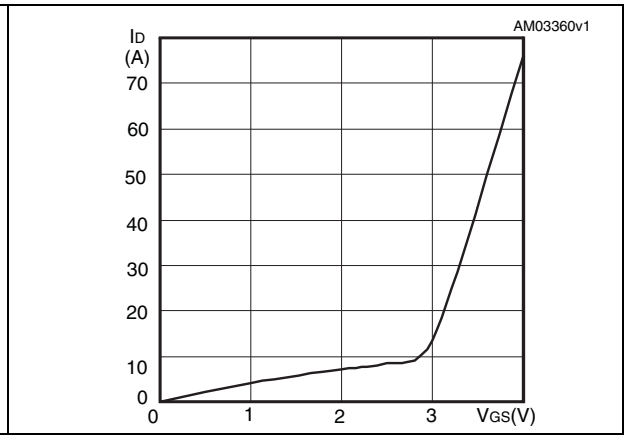


Figure 6. Normalized B_{VDSS} vs temperature

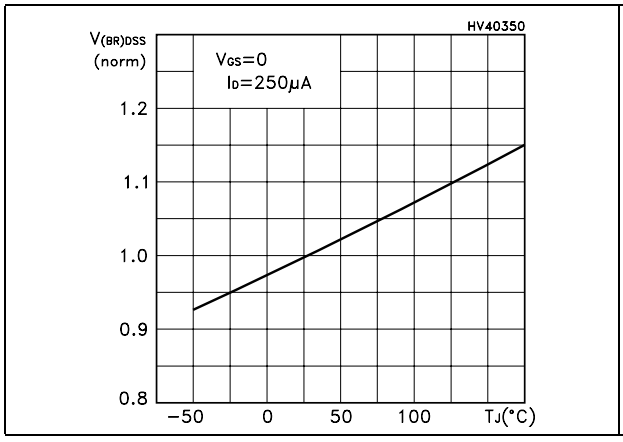


Figure 7. Static drain-source on resistance